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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, Ethernet, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	DMA, POR, PWM, Voltage Detect, WDT
Number of I/O	80
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f107vct6tr

List of figures

Figure 1.	STM32F105xx and STM32F107xx connectivity line block diagram	13
Figure 2.	STM32F105xx and STM32F107xx connectivity line BGA100 ballout top view	24
Figure 3.	STM32F105xx and STM32F107xx connectivity line LQFP100 pinout	25
Figure 4.	STM32F105xx and STM32F107xx connectivity line LQFP64 pinout	26
Figure 5.	Memory map	33
Figure 6.	Pin loading conditions	34
Figure 7.	Pin input voltage	34
Figure 8.	Power supply scheme	35
Figure 9.	Current consumption measurement scheme	35
Figure 10.	Typical current consumption on V_{BAT} with RTC on vs. temperature at different V_{BAT} values	42
Figure 11.	Typical current consumption in Stop mode with regulator in Run mode versus temperature at different V_{DD} values	42
Figure 12.	Typical current consumption in Stop mode with regulator in Low-power mode versus temperature at different V_{DD} values	43
Figure 13.	Typical current consumption in Standby mode versus temperature at different V_{DD} values	43
Figure 14.	High-speed external clock source AC timing diagram	48
Figure 15.	Low-speed external clock source AC timing diagram	49
Figure 16.	Typical application with an 8 MHz crystal	50
Figure 17.	Typical application with a 32.768 kHz crystal	51
Figure 18.	Standard I/O input characteristics - CMOS port	58
Figure 19.	Standard I/O input characteristics - TTL port	59
Figure 20.	5 V tolerant I/O input characteristics - CMOS port	59
Figure 21.	5 V tolerant I/O input characteristics - TTL port	59
Figure 22.	I/O AC characteristics definition	62
Figure 23.	Recommended NRST pin protection	63
Figure 24.	I ² C bus AC waveforms and measurement circuit	65
Figure 25.	SPI timing diagram - slave mode and CPHA = 0	67
Figure 26.	SPI timing diagram - slave mode and CPHA = 1 ⁽¹⁾	67
Figure 27.	SPI timing diagram - master mode ⁽¹⁾	68
Figure 28.	I ² S slave timing diagram (Philips protocol) ⁽¹⁾	70
Figure 29.	I ² S master timing diagram (Philips protocol) ⁽¹⁾	70
Figure 30.	USB OTG FS timings: definition of data signal rise and fall time	71
Figure 31.	Ethernet SMI timing diagram	72
Figure 32.	Ethernet RMII timing diagram	73
Figure 33.	Ethernet MII timing diagram	73
Figure 34.	ADC accuracy characteristics	77
Figure 35.	Typical connection diagram using the ADC	77
Figure 36.	Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})	78
Figure 37.	Power supply and reference decoupling (V_{REF+} connected to V_{DDA})	78
Figure 38.	12-bit buffered /non-buffered DAC	80
Figure 39.	LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline	82
Figure 40.	LFBGA100 – 100-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data	83
Figure 41.	LFBGA100 – 100-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package recommended footprint	83

2.2 Full compatibility throughout the family

The STM32F105xx and STM32F107xx constitute the connectivity line family whose members are fully pin-to-pin, software and feature compatible.

The STM32F105xx and STM32F107xx are a drop-in replacement for the low-density (STM32F103x4/6), medium-density (STM32F103x8/B) and high-density (STM32F103xC/D/E) performance line devices, allowing the user to try different memory densities and peripherals providing a greater degree of freedom during the development cycle.

Table 3. STM32F105xx and STM32F107xx family versus STM32F103xx family⁽¹⁾

STM32 device	Low-density STM32F103xx devices		Medium-density STM32F103xx devices			High-density STM32F103xx devices			STM32F105xx			STM32F107xx			
Flash size (KB)	16	32	32	64	128	256	384	512	64	128	256	128	256		
RAM size (KB)	6	10	10	20	20	48	64	64	64	64	64	64	64		
144 pins						5 × USARTs 4 × 16-bit timers, 2 × basic timers, 3 × SPIs, 2 × I ² Ss, 2 × I2Cs, USB, CAN, 2 × PWM timers 3 × ADCs, 2 × DACs, 1 × SDIO, FSMC (100- and 144-pin packages ⁽²⁾)			5 × USARTs, 4 × 16-bit timers, 2 × basic timers, 3 × SPIs, 2 × I ² Ss, 2 × I2Cs, USB OTG FS, 2 × CANs, 1 × PWM timer, 2 × ADCs, 2 × DACs					5 × USARTs, 4 × 16-bit timers, 2 × basic timers, 3 × SPIs, 2 × I ² S, 1 × I2C, USB OTG FS, 2 × CANs, 1 × PWM timer, 2 × ADCs, 2 × DACs, Ethernet	
100 pins															
64 pins															
48 pins	2 × USARTs 2 × 16-bit timers 1 × SPI, 1 × I ² C, USB, CAN, 1 × PWM timer 2 × ADCs		2 × USARTs 2 × 16-bit timers 1 × SPI, 1 × I ² C, USB, CAN, 1 × PWM timer 2 × ADCs		3 × USARTs 3 × 16-bit timers 2 × SPIs, 2 × I ² Cs, USB, CAN, 1 × PWM timer 2 × ADCs										
36 pins															

1. Refer to [Table 5: Pin definitions](#) for peripheral availability when the I/O pins are shared by the peripherals required by the application.
2. Ports F and G are not available in devices delivered in 100-pin packages.

2.3.6 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 20 edge detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 80 GPIOs can be connected to the 16 external interrupt lines.

2.3.7 Clocks and startup

System clock selection is performed on startup, however, the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 3-25 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example with failure of an indirectly used external oscillator).

A single 25 MHz crystal can clock the entire system including the ethernet and USB OTG FS peripherals. Several prescalers and PLLs allow the configuration of the AHB frequency, the high speed APB (APB2) and the low speed APB (APB1) domains. The maximum frequency of the AHB and the high speed APB domains is 72 MHz. The maximum allowed frequency of the low speed APB domain is 36 MHz. Refer to [Figure 59: USB OTG FS + Ethernet solution on page 100](#).

The advanced clock controller clocks the core and all peripherals using a single crystal or oscillator. In order to achieve audio class performance, an audio crystal can be used. In this case, the I²S master clock can generate all standard sampling frequencies from 8 kHz to 96 kHz with less than 0.5% accuracy error. Refer to [Figure 60: USB OTG FS + I2S \(Audio\) solution on page 100](#).

To configure the PLLs, refer to [Table 63 on page 101](#), which provides PLL configurations according to the application type.

2.3.8 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from User Flash
- Boot from System Memory
- Boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1, USART2 (remapped), CAN2 (remapped) or USB OTG FS in device mode (DFU: device firmware upgrade). For remapped signals refer to [Table 5: Pin definitions](#).

The USART peripheral operates with the internal 8 MHz oscillator (HSI), however the CAN and USB OTG FS can only function if an external 8 MHz, 14.7456 MHz or 25 MHz clock (HSE) is present.

For full details about the boot loader, refer to AN2606.

Any of the standard timers can be used to generate PWM outputs. Each of the timers has independent DMA request generations.

Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as a generic 16-bit time base.

Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.3.16 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.17 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F105xx and STM32F107xx connectivity line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability.

The USART1 interface is able to communicate at speeds of up to 4.5 Mbit/s. The other available interfaces communicate at up to 2.25 Mbit/s.

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\Sigma$).

5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$ (for the $2\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\Sigma$).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 6](#).

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 7](#).

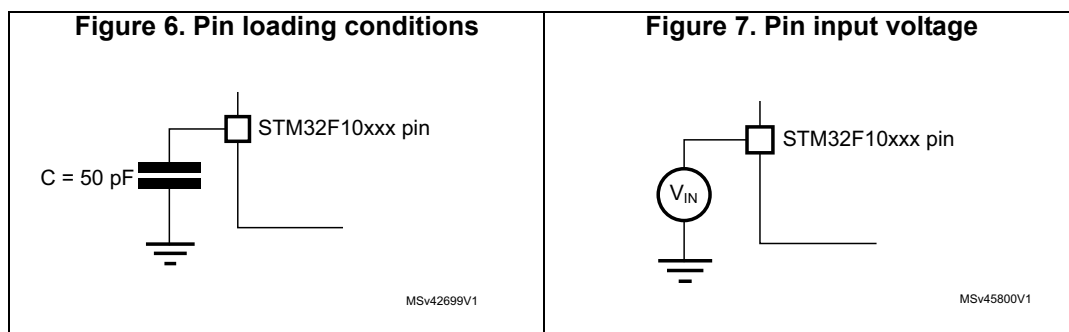


Table 8. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C

5.3 Operating conditions

5.3.1 General operating conditions

Table 9. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	72	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	36	
f_{PCLK2}	Internal APB2 clock frequency	-	0	72	
V_{DD}	Standard operating voltage	-	2	3.6	V
$V_{DDA}^{(1)}$	Analog operating voltage (ADC not used)	Must be the same potential as $V_{DD}^{(2)}$	2	3.6	V
	Analog operating voltage (ADC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.8	3.6	V
P_D	Power dissipation at $T_A = 85\text{ °C}$ for suffix 6 or $T_A = 105\text{ °C}$ for suffix 7 ⁽³⁾	LFBGA100	-	500	mW
		LQFP100	-	434	
		LQFP64	-	444	
P_D	Power dissipation at $T_A = 85\text{ °C}$ for suffix 6 or $T_A = 105\text{ °C}$ for suffix 7 ⁽⁴⁾	LQFP100	-	434	mW
		LQFP64	-	444	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	-40	85	°C
		Low power dissipation ⁽⁵⁾	-40	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	-40	105	°C
		Low power dissipation ⁽⁵⁾	-40	125	
T_J	Junction temperature range	6 suffix version	-40	105	°C
		7 suffix version	-40	125	

1. When the ADC is used, refer to [Table 52: ADC characteristics](#).
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.
3. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} .
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} .
5. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} .

5.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A .

Table 10. Operating condition at power-up / power down

Symbol	Parameter	Condition	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	-	$\mu\text{s/V}$
T_J	V_{DD} fall time rate		20	-	

5.3.3 Embedded reset and power control block characteristics

The parameters given in [Table 11](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 11. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.1	2.18	2.26	V
		PLS[2:0]=000 (falling edge)	2	2.08	2.16	V
		PLS[2:0]=001 (rising edge)	2.19	2.28	2.37	V
		PLS[2:0]=001 (falling edge)	2.09	2.18	2.27	V
		PLS[2:0]=010 (rising edge)	2.28	2.38	2.48	V
		PLS[2:0]=010 (falling edge)	2.18	2.28	2.38	V
		PLS[2:0]=011 (rising edge)	2.38	2.48	2.58	V
		PLS[2:0]=011 (falling edge)	2.28	2.38	2.48	V
		PLS[2:0]=100 (rising edge)	2.47	2.58	2.69	V
		PLS[2:0]=100 (falling edge)	2.37	2.48	2.59	V
		PLS[2:0]=101 (rising edge)	2.57	2.68	2.79	V
		PLS[2:0]=101 (falling edge)	2.47	2.58	2.69	V
		PLS[2:0]=110 (rising edge)	2.66	2.78	2.9	V
		PLS[2:0]=110 (falling edge)	2.56	2.68	2.8	V
		PLS[2:0]=111 (rising edge)	2.76	2.88	3	V
		PLS[2:0]=111 (falling edge)	2.66	2.78	2.9	V
$V_{PVDhyst}^{(2)}$	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1.8 ⁽¹⁾	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	V
$V_{PDRhyst}^{(2)}$	PDR hysteresis	-	-	40	-	mV
$T_{RSTTEMPO}^{(2)}$	Reset temporization	-	1	2.5	4.5	ms

1. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.

2. Guaranteed by design, not tested in production.

Table 13. Maximum current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions	f_{HCLK}	Max ⁽¹⁾		Unit
				$T_A = 85\text{ °C}$	$T_A = 105\text{ °C}$	
I_{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled	72 MHz	68	68.4	mA
			48 MHz	49	49.2	
			36 MHz	38.7	38.9	
			24 MHz	27.3	27.9	
			16 MHz	20.2	20.5	
			8 MHz	10.2	10.8	
		External clock ⁽²⁾ , all peripherals disabled	72 MHz	32.7	32.9	
			48 MHz	25	25.2	
			36 MHz	20.3	20.6	
			24 MHz	14.8	15.1	
			16 MHz	11.2	11.7	
			8 MHz	6.6	7.2	

1. Based on characterization, not tested in production.

2. External clock is 8 MHz and PLL is on when $f_{HCLK} > 8\text{ MHz}$.

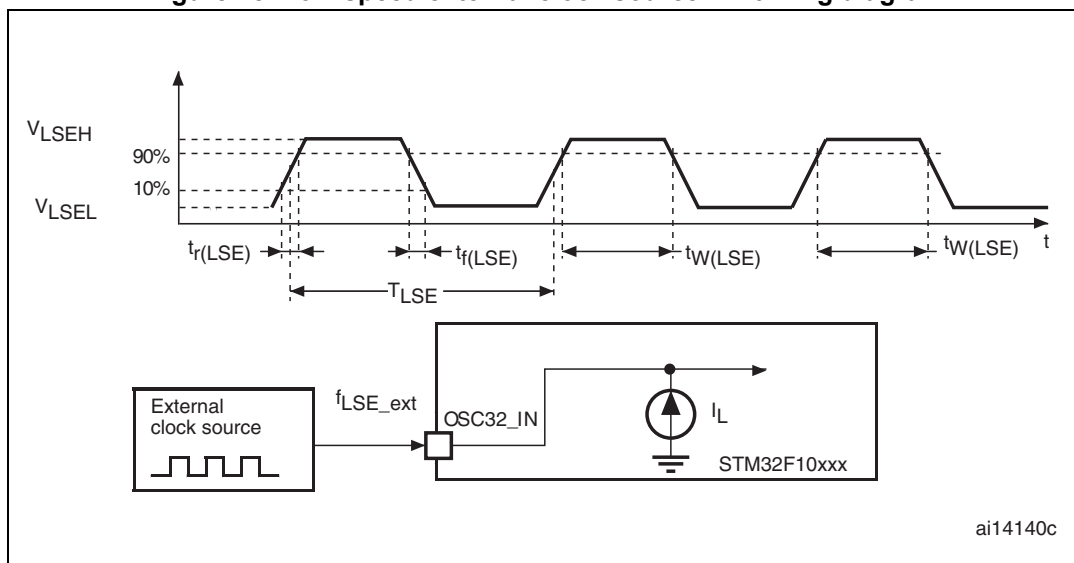
Table 14. Maximum current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions	f_{HCLK}	Max ⁽¹⁾		Unit
				$T_A = 85\text{ °C}$	$T_A = 105\text{ °C}$	
I_{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled	72 MHz	65.5	66	mA
			48 MHz	45.4	46	
			36 MHz	35.5	36.1	
			24 MHz	25.2	25.6	
			16 MHz	18	18.5	
			8 MHz	10.5	11	
		External clock ⁽²⁾ , all peripherals disabled	72 MHz	31.4	31.9	
			48 MHz	27.8	28.2	
			36 MHz	17.6	18.3	
			24 MHz	13.1	13.8	
			16 MHz	10.2	10.9	
			8 MHz	6.1	7.8	

1. Based on characterization, tested in production at V_{DD} max, f_{HCLK} max..

2. External clock is 8 MHz and PLL is on when $f_{HCLK} > 8\text{ MHz}$.

Figure 15. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 3 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 22](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 22. HSE 3-25 MHz oscillator characteristics^{(1) (2)}

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	3		25	MHz
R_F	Feedback resistor	-	-	200	-	k Ω
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) ⁽³⁾	$R_S = 30 \Omega$	-	30	-	pF
i_2	HSE driving current	$V_{DD} = 3.3 V, V_{IN} = V_{SS}$ with 30 pF load	-	-	1	mA
g_m	Oscillator transconductance	Startup	25	-	-	mA/V
$t_{SU(HSE)}$ ⁽⁴⁾	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization, not tested in production.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

Table 23. LSE oscillator characteristics ($f_{LSE} = 32.768 \text{ kHz}$) ⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{SU(LSE)}$ (4)	Startup time	V_{DD} is stabilized	$T_A = 50 \text{ }^\circ\text{C}$	-	1.5	-
			$T_A = 25 \text{ }^\circ\text{C}$	-	2.5	-
			$T_A = 10 \text{ }^\circ\text{C}$	-	4	-
			$T_A = 0 \text{ }^\circ\text{C}$	-	6	-
			$T_A = -10 \text{ }^\circ\text{C}$	-	10	-
			$T_A = -20 \text{ }^\circ\text{C}$	-	17	-
			$T_A = -30 \text{ }^\circ\text{C}$	-	32	-
			$T_A = -40 \text{ }^\circ\text{C}$	-	60	-

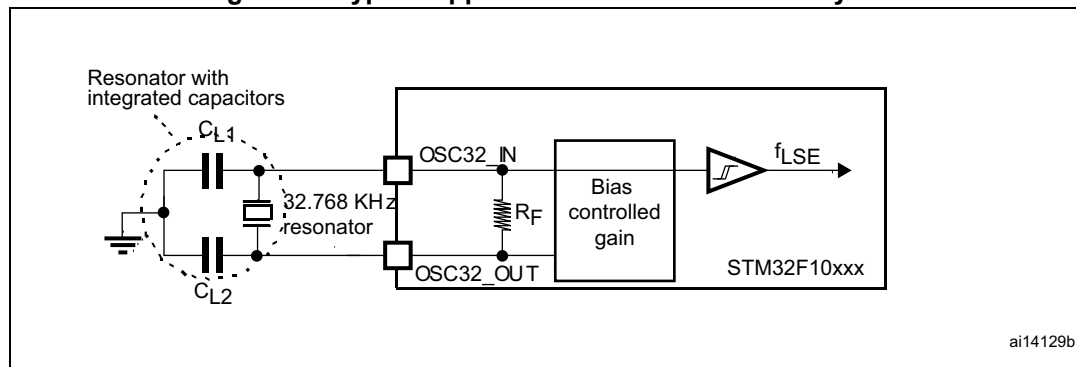
1. Based on characterization, not tested in production.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details
4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For C_{L1} and C_{L2} it is recommended to use high-quality external ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 17). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7 \text{ pF}$. Never use a resonator with a load capacitance of 12.5 pF.

Example: if you choose a resonator with a load capacitance of $C_L = 6 \text{ pF}$, and $C_{stray} = 2 \text{ pF}$, then $C_{L1} = C_{L2} = 8 \text{ pF}$.

Figure 17. Typical application with a 32.768 kHz crystal



ai14129b

Figure 19. Standard I/O input characteristics - TTL port

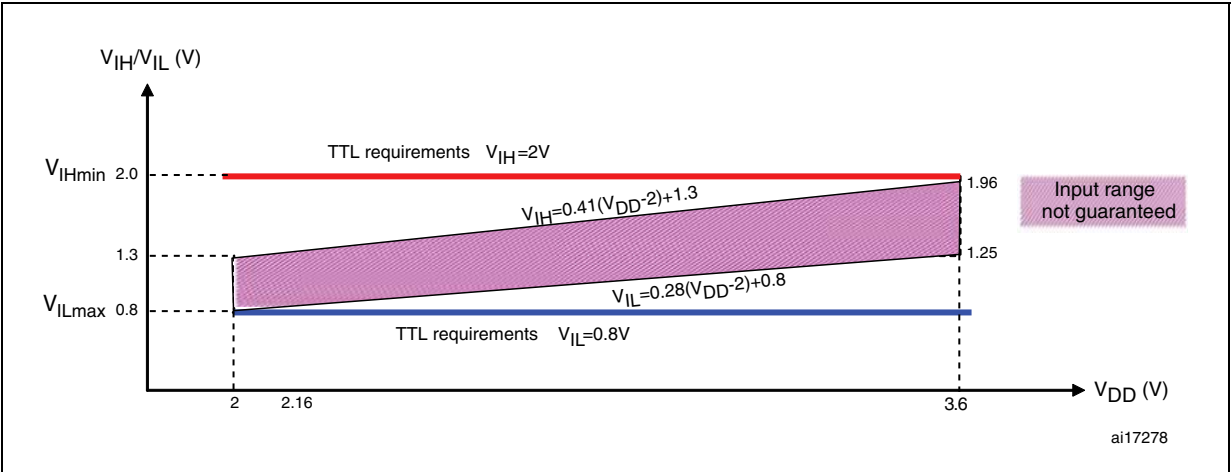


Figure 20. 5 V tolerant I/O input characteristics - CMOS port

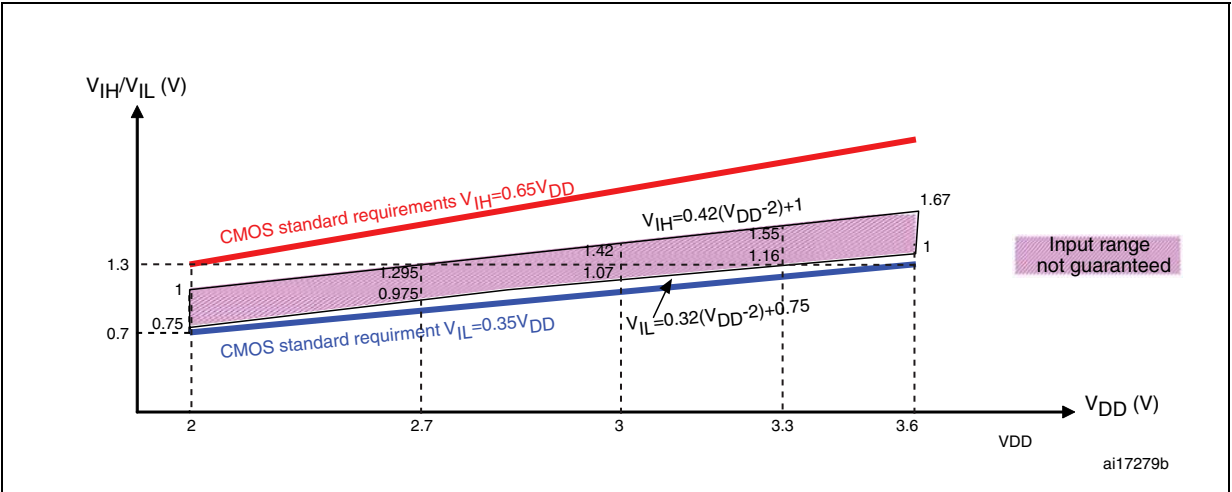


Figure 21. 5 V tolerant I/O input characteristics - TTL port

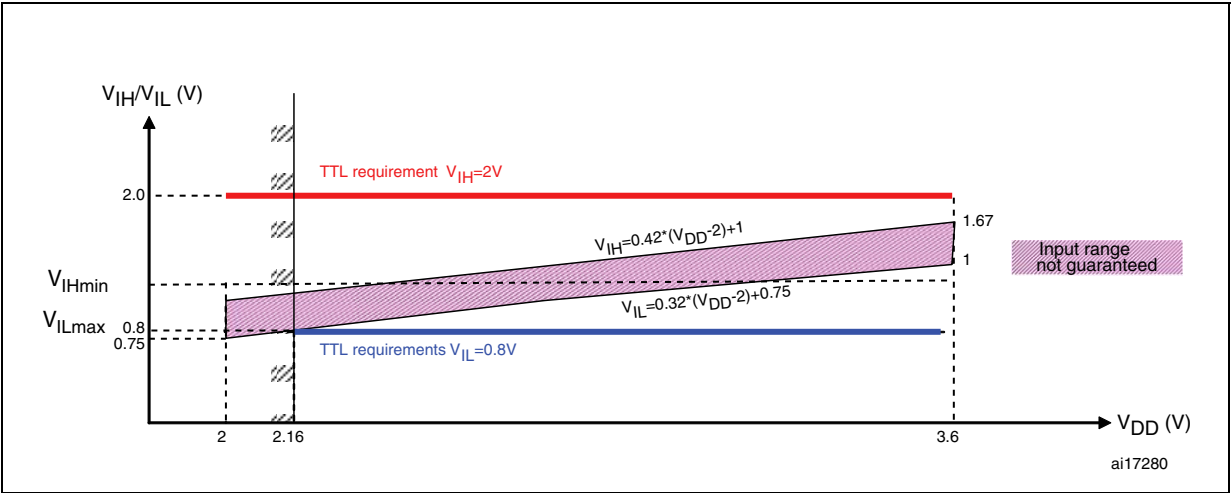
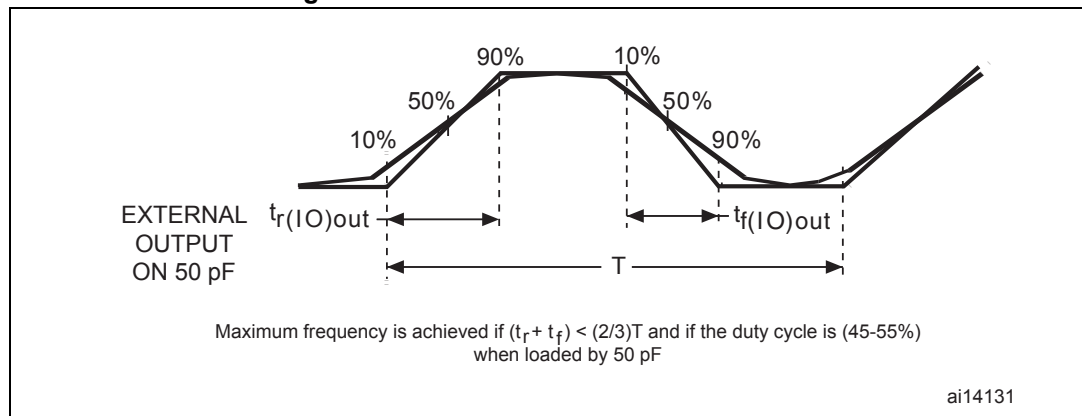


Figure 22. I/O AC characteristics definition



5.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 36](#)).

Unless otherwise specified, the parameters given in [Table 39](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

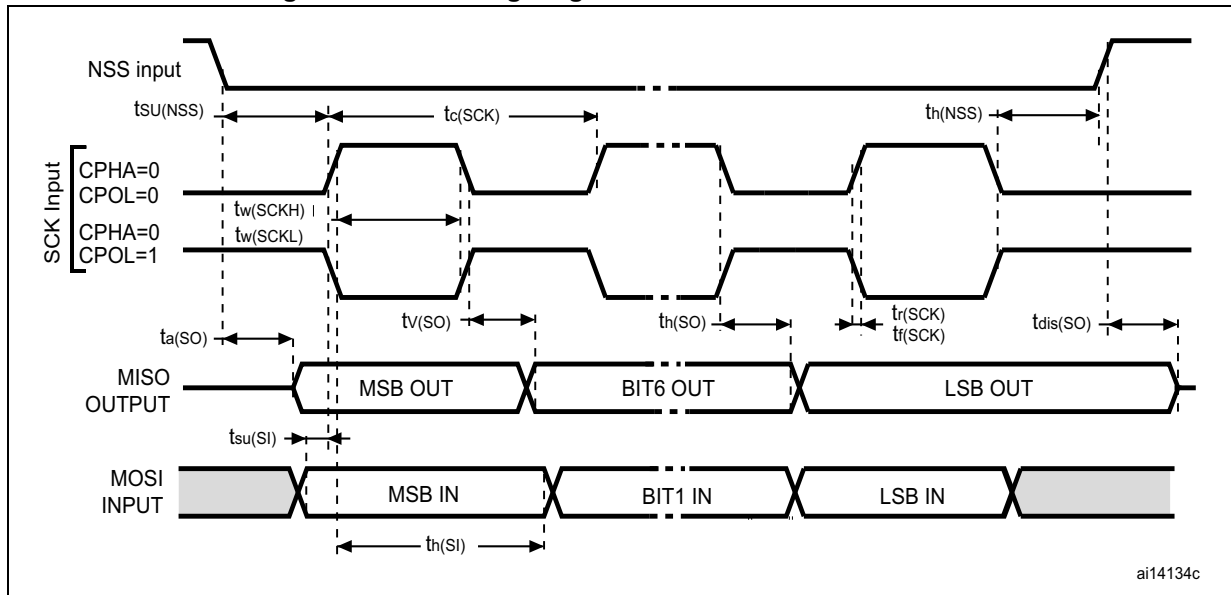
Table 39. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST Input low level voltage	-	-0.5	-	0.8	V
$V_{IH(NRST)}^{(1)}$	NRST Input high level voltage	-	2	-	$V_{DD}+0.5$	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽²⁾	$V_{IN} = V_{SS}$	30	40	50	k Ω
$V_{F(NRST)}^{(1)}$	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}^{(1)}$	NRST Input not filtered pulse	$V_{DD} > 2.7$ V	300	-	-	ns

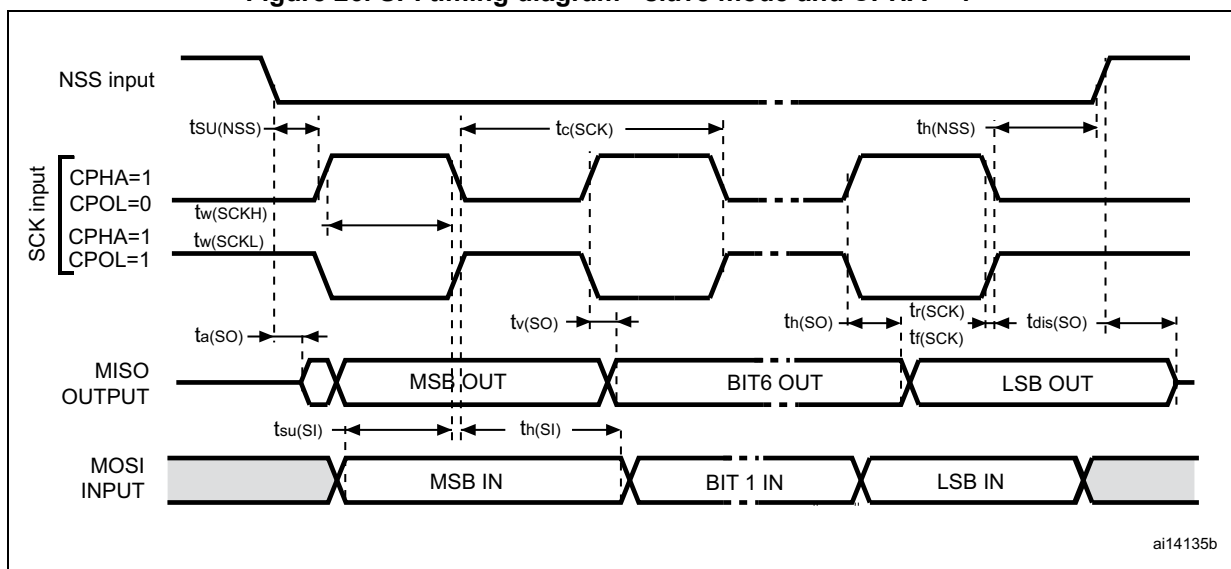
1. Guaranteed by design, not tested in production.

2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

Figure 25. SPI timing diagram - slave mode and CPHA = 0



ai14134c

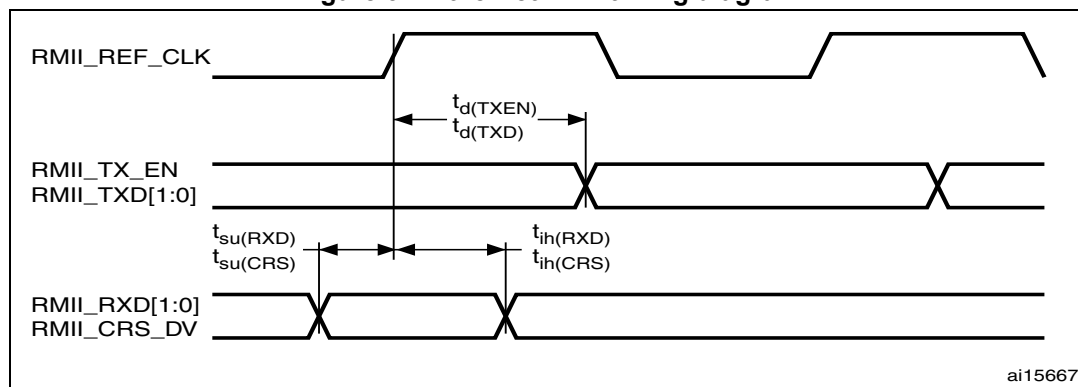
Figure 26. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾

ai14135b

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 50 gives the list of Ethernet MAC signals for the RMI and Figure 32 shows the corresponding timing diagram.

Figure 32. Ethernet RMI timing diagram



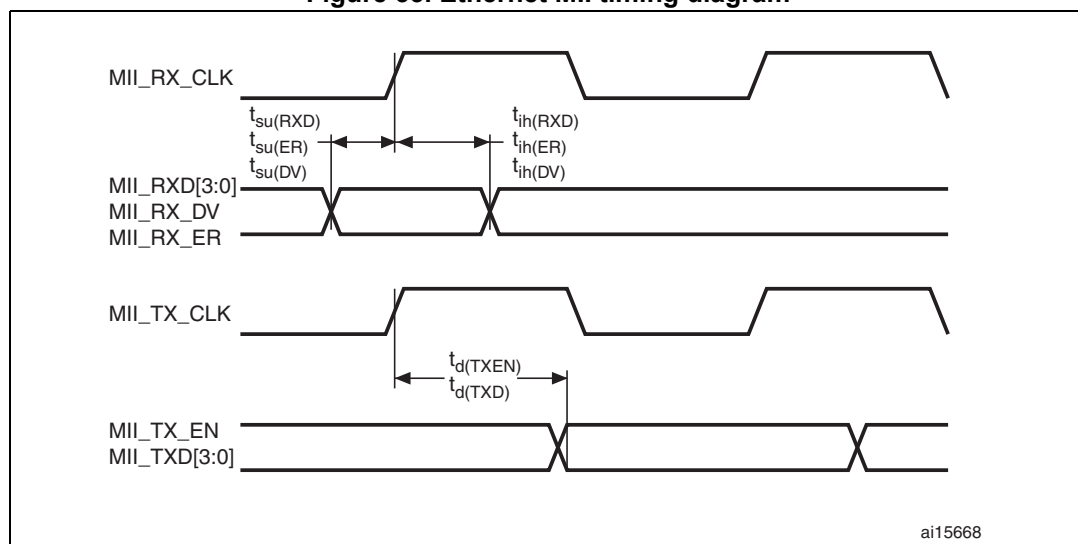
ai15667

Table 50. Dynamic characteristics: Ethernet MAC signals for RMI

Symbol	Rating	Min	Typ	Max	Unit
$t_{su}(RXD)$	Receive data setup time	4	-	-	ns
$t_{ih}(RXD)$	Receive data hold time	2	-	-	ns
$t_{su}(DV)$	Carrier sense set-up time	4	-	-	ns
$t_{ih}(DV)$	Carrier sense hold time	2	-	-	ns
$t_d(TXEN)$	Transmit enable valid delay time	8	10	16	ns
$t_d(TXD)$	Transmit data valid delay time	7	10	16	ns

Table 51 gives the list of Ethernet MAC signals for MII and Figure 33 shows the corresponding timing diagram.

Figure 33. Ethernet MII timing diagram



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Table 52. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{lat}^{(2)}$	Injection trigger conversion latency	$f_{ADC} = 14 \text{ MHz}$	-	-	0.214	μs
		-	-	-	3 ⁽⁴⁾	$1/f_{ADC}$
$t_{latr}^{(2)}$	Regular trigger conversion latency	$f_{ADC} = 14 \text{ MHz}$	-	-	0.143	μs
		-	-	-	2 ⁽⁴⁾	$1/f_{ADC}$
$t_S^{(2)}$	Sampling time	$f_{ADC} = 14 \text{ MHz}$	0.107	-	17.1	μs
		-	1.5	-	239.5	$1/f_{ADC}$
$t_{STAB}^{(2)}$	Power-up time	-	0	0	1	μs
$t_{CONV}^{(2)}$	Total conversion time (including sampling time)	$f_{ADC} = 14 \text{ MHz}$	1	-	18	μs
		-	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. Based on characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} .
4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in [Table 52](#).

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here $N = 12$ (from 12-bit resolution).

Table 53. R_{AIN} max for $f_{ADC} = 14 \text{ MHz}$ ⁽¹⁾

T_S (cycles)	t_S (μs)	R_{AIN} max ($k\Omega$)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

1. Based on characterization, not tested in production.

Table 54. ADC accuracy - limited test conditions⁽¹⁾

Symbol	Parameter	Test conditions	Typ	Max ⁽²⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 14 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$ $V_{DDA} = 3 \text{ V to } 3.6 \text{ V}$ $T_A = 25 \text{ }^\circ\text{C}$ Measurements made after ADC calibration	± 1.3	± 2	LSB
EO	Offset error		± 1	± 1.5	
EG	Gain error		± 0.5	± 1.5	
ED	Differential linearity error		± 0.7	± 1	
EL	Integral linearity error		± 0.8	± 1.5	

1. ADC DC accuracy values are measured after internal calibration.

2. Based on characterization, not tested in production.

Table 55. ADC accuracy^{(1) (2)}

Symbol	Parameter	Test conditions	Typ	Max ⁽³⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 14 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$ $V_{DDA} = 2.4 \text{ V to } 3.6 \text{ V}$ Measurements made after ADC calibration	± 2	± 5	LSB
EO	Offset error		± 1.5	± 2.5	
EG	Gain error		± 1.5	± 3	
ED	Differential linearity error		± 1	± 2	
EL	Integral linearity error		± 1.5	± 3	

1. ADC DC accuracy values are measured after internal calibration.

2. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.

3. Based on characterization, not tested in production.

Note:

ADC accuracy vs. negative injection current: Injecting a negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative currents.

Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 5.3.12](#) does not affect the ADC accuracy.

Figure 34. ADC accuracy characteristics

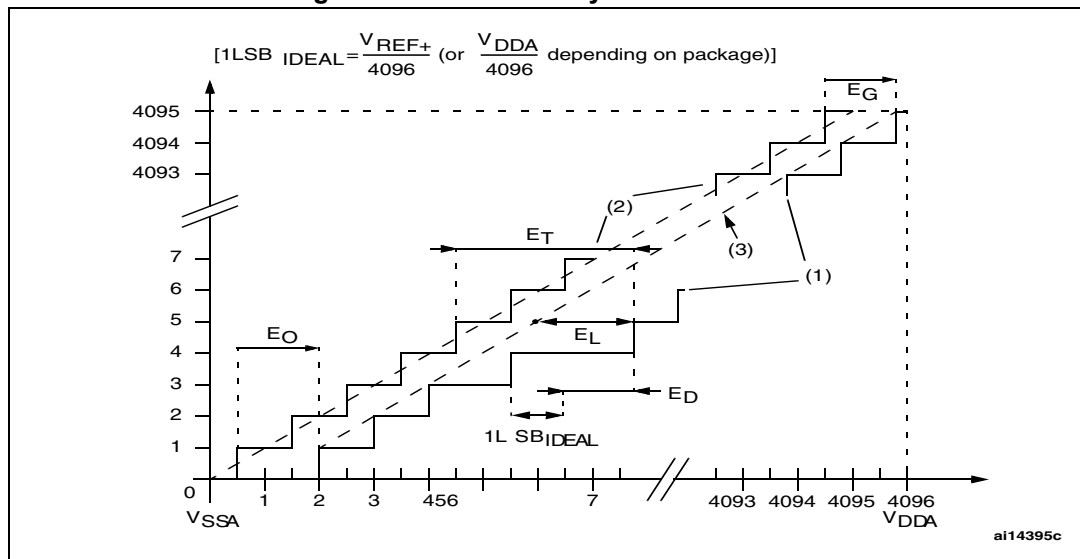
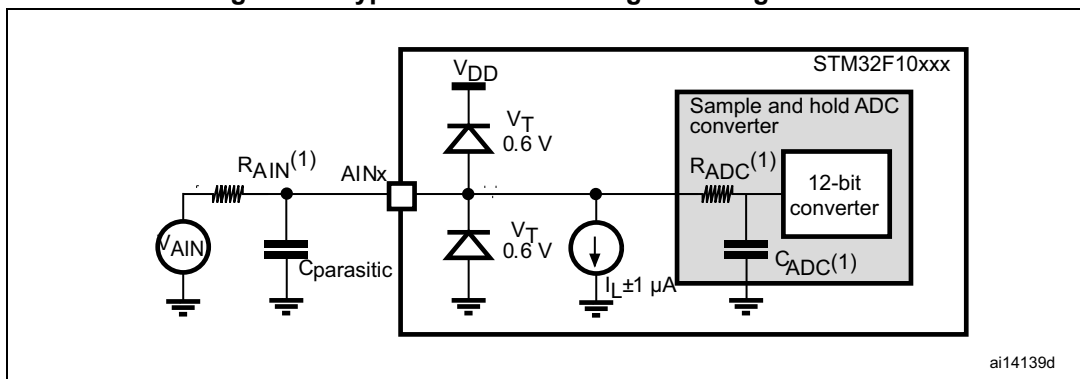


Figure 35. Typical connection diagram using the ADC



1. Refer to [Table 52](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

5.3.19 Temperature sensor characteristics

Table 57. TS characteristics

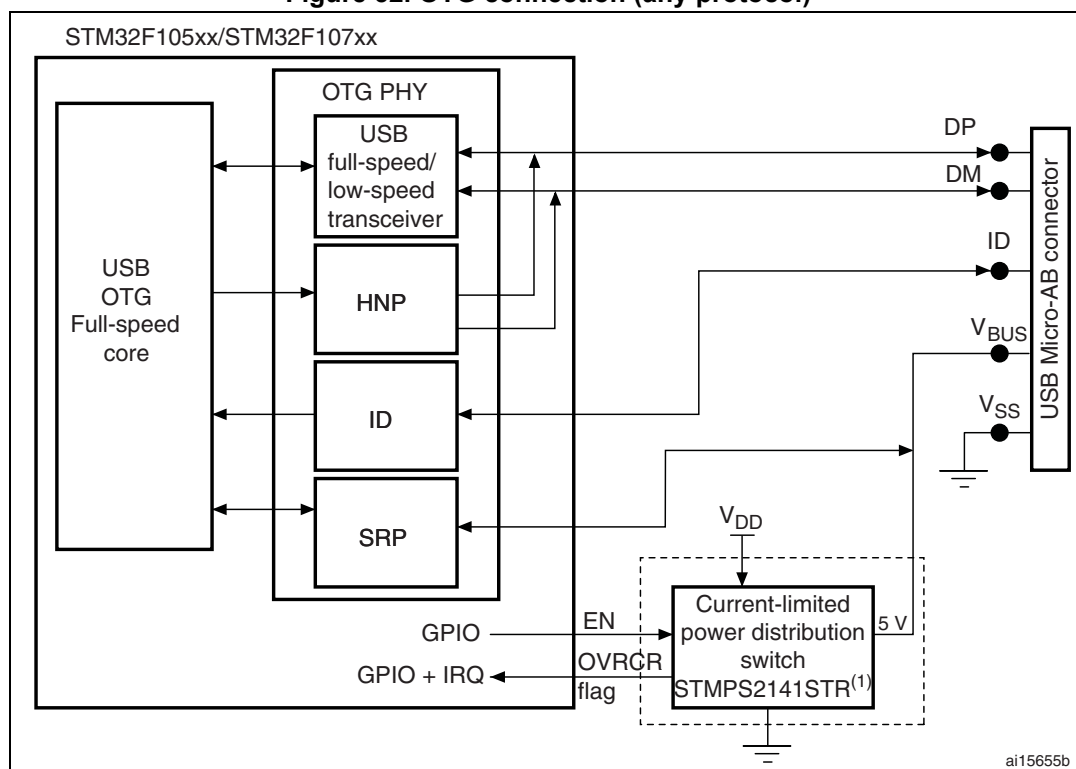
Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope ⁽¹⁾	Average slope	4.0	4.3	4.6	mV/°C
$V_{25}^{(1)}$	Voltage at 25 °C	1.34	1.43	1.52	V
$t_{START}^{(2)}$	Startup time	4	-	10	μs
$T_{S_temp}^{(3)(2)}$	ADC sampling time when reading the temperature	-	-	17.1	μs

1. Based on characterization, not tested in production.

2. Guaranteed by design, not tested in production.

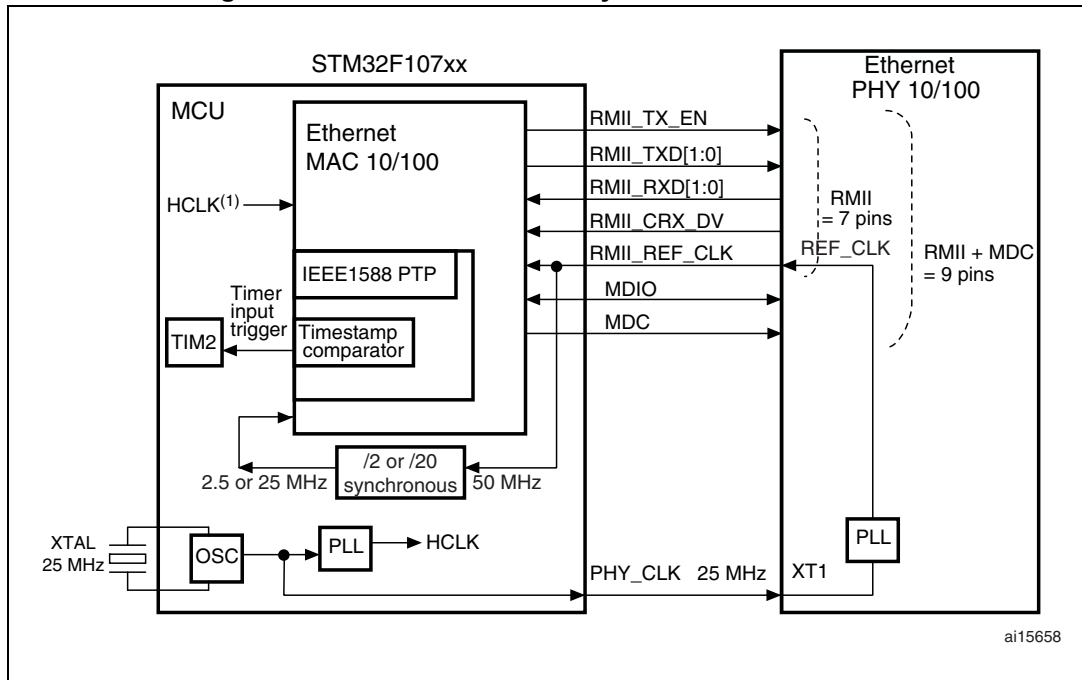
3. Shortest sampling time can be determined in the application by multiple iterations.

Figure 52. OTG connection (any protocol)



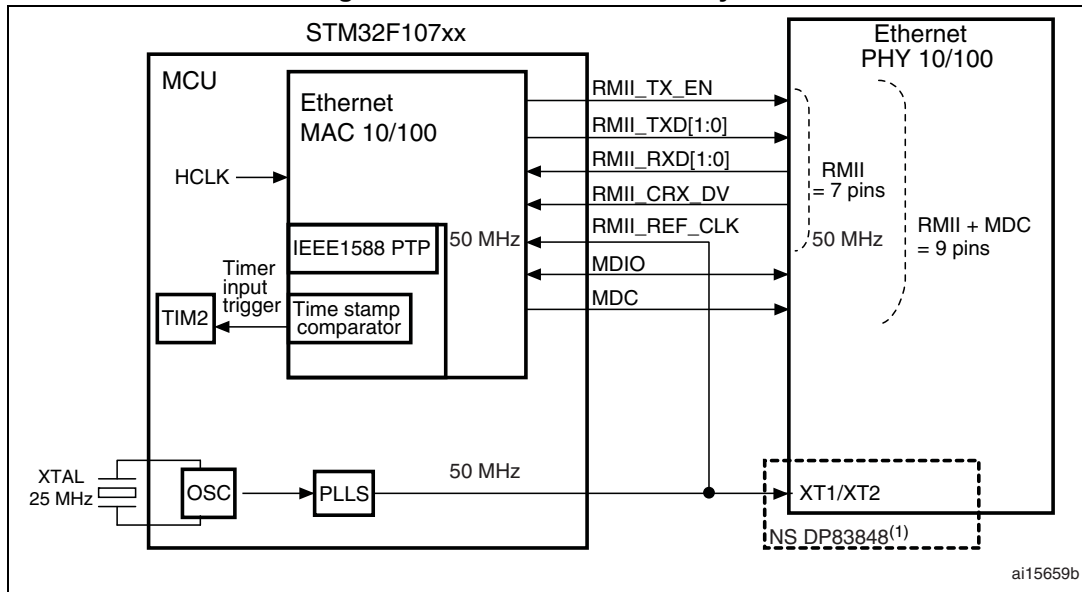
1. STMP2141STR needed only if the application has to support bus-powered devices.

Figure 55. RMI1 with a 25 MHz crystal and PHY with PLL



1. HCLK must be greater than 25 MHz.

Figure 56. RMII with a 25 MHz crystal



1. The NS DP83848 is recommended as the input jitter requirement of this PHY. It is compliant with the output jitter specification of the MCU.